



SURFACE-MOUNT PNP POWER TRANSISTORS

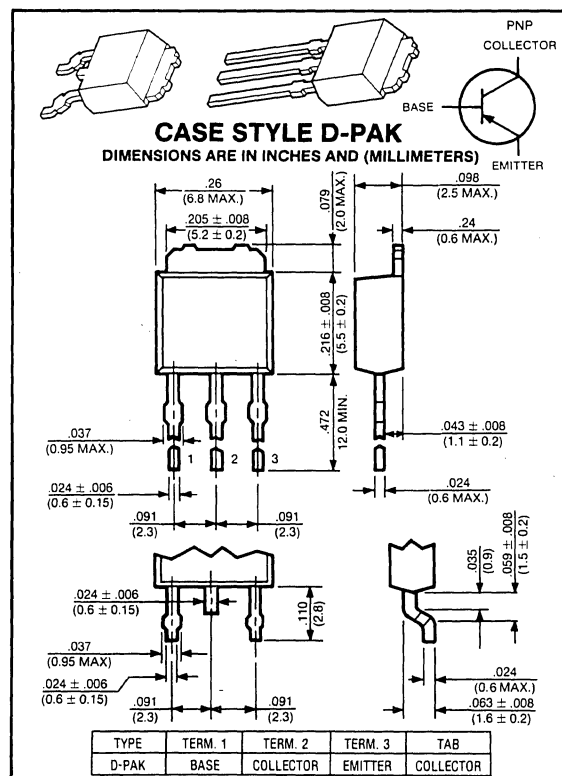
D73F5T1,2

**-50 VOLTS
-5 AMP, 20 WATTS**

Designed for high current switching applications.

Features:

- Low Collector Saturation Voltage
: $V_{CE(sat)} = -0.4V$ (Max.) (at $I_C = 3A$)
- High Speed Switching Time : $t_{stg} = 1.0\mu s$ (Typ.)
- Complementary to D72F5T1,2
- Suffix "2" designates lead formed version
- See page 840 for mounting and handling considerations.



maximum ratings ($T_A = 25^\circ C$) (unless otherwise specified)

RATING	SYMBOL	D73F5T1,2	UNITS
Collector-Emitter Voltage	V_{CEO}	-50	Volts
Collector-Base Voltage	V_{CBO}	-60	Volts
Emitter Base Voltage	V_{EBO}	-5	Volts
Collector Current — Continuous	I_C	-5	A
Base Current — Continuous	I_B	-1	A
Total Power Dissipation @ $T_C = 25^\circ C$ @ $T_C = 25^\circ C$	P_D	1.0 20	Watts
Operating and Storage Junction Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ C$

thermal characteristics⁽¹⁾

Maximum Lead Temperature for Soldering Purposes: $\frac{1}{8}$ " from Case for 5 Seconds	T_L	235	$^\circ C$
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(1) See page 841 for thermal considerations.

electrical characteristics ($T_A = 25^\circ\text{C}$) (unless otherwise specified)

CHARACTERISTIC	SYMBOL	MIN	TYP	MAX	UNIT
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off characteristics

Collector-Emitter Breakdown Voltage ($I_C = 10\text{mA}$, $I_B = 0$)	$V_{(BR)CEO}$	-50	—	—	Volts
Collector Cutoff Current ($V_{CB} = 50\text{V}$, $I_E = 0$)	I_{CBO}	—	—	-1	μA
Emitter Cutoff Current ($V_{EB} = 5\text{V}$, $I_C = 0$)	I_{EBO}	—	—	-1	μA

second breakdown

Second Breakdown with Base Forward Biased	FBSOA	SEE FIGURE 11
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on characteristics

DC Current Gain ⁽²⁾ ($I_C = -1\text{A}$, $V_{CE} = -1\text{V}$) ($I_C = -3\text{A}$, $V_{CE} = -1\text{V}$)	h_{FE} h_{FE}	70 30	— —	240 —	—
Collector-Emitter Saturation Voltage ($I_C = -3\text{A}$, $I_B = -0.15\text{A}$)	$V_{CE(sat)}$	—	-0.2	-0.4	V
Base-Emitter Saturation Voltage ($I_C = -3\text{A}$, $I_B = -0.15\text{A}$)	$V_{BE(sat)}$	—	-0.9	-1.2	Volts

switching characteristics

Turn-on Time	$V_{CC} = -30\text{V}$	t_{on}	—	0.1	—	μs
Storage Time	$-I_{B1} = I_{B2} = 0.15\text{A}$	t_{stg}	—	1.0	—	
Fall Time	Duty Cycle $\leq 1\%$	t_f	—	0.1	—	

(2) See page 43 for h_{FE} ranges.

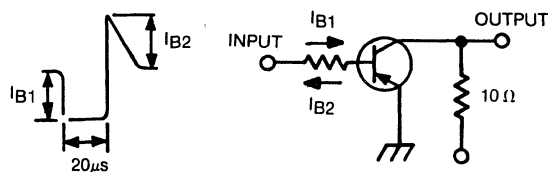


FIG. 1 SWITCHING TIME TEST CIRCUIT

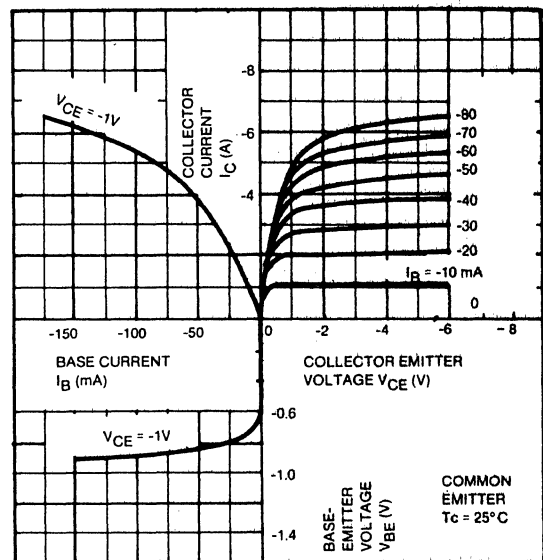


FIG. 2 STATIC CHARACTERISTICS

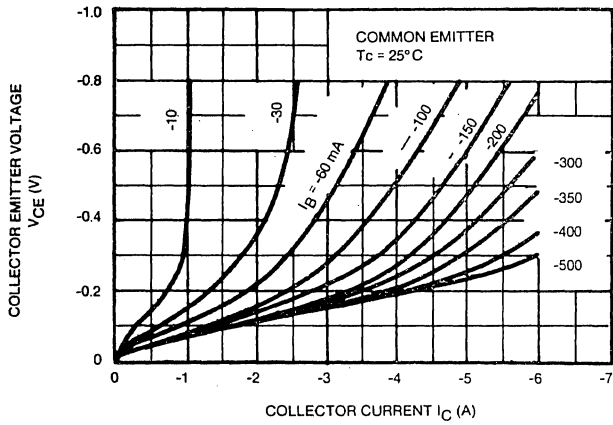


FIG. 3 V_{CE} - I_C

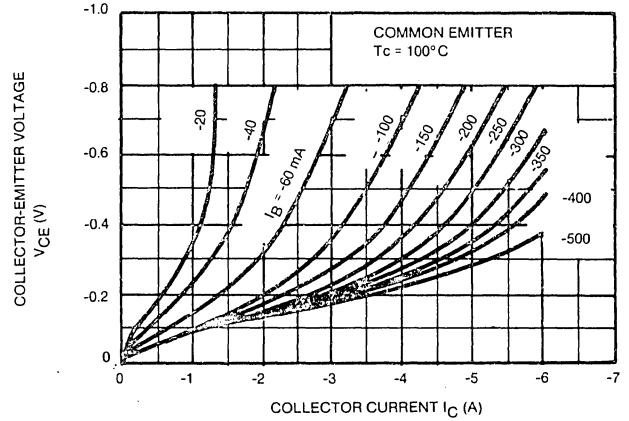


FIG. 4 V_{CE} - I_C

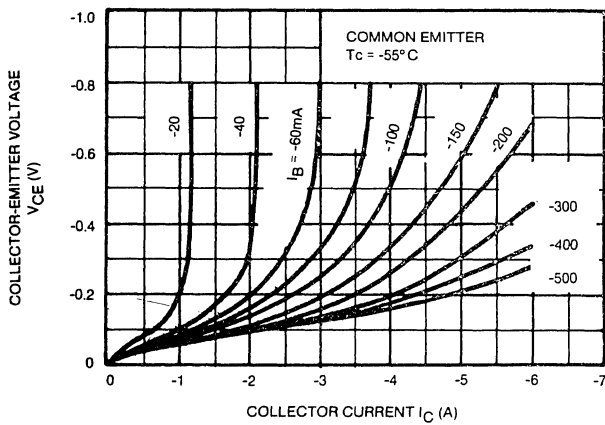


FIG. 5 V_{CE} - I_C

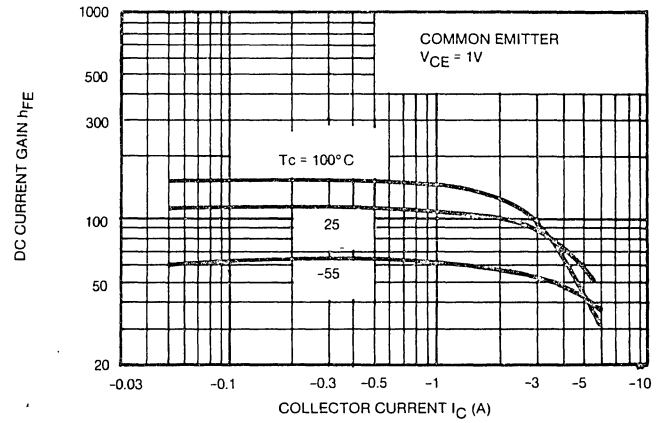


FIG. 6 h_{FE} - I_C

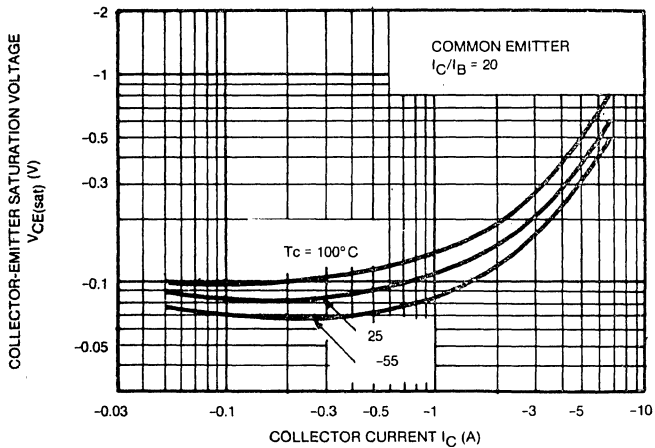


FIG. 7 V_{CE(sat)} - I_C

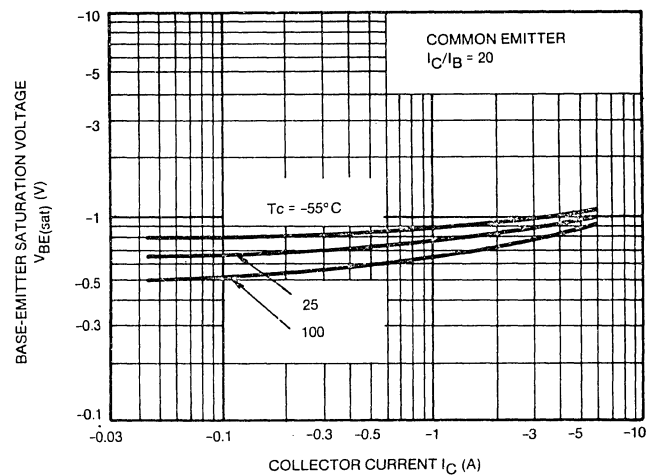


FIG. 8 V_{BE(sat)} - I_C

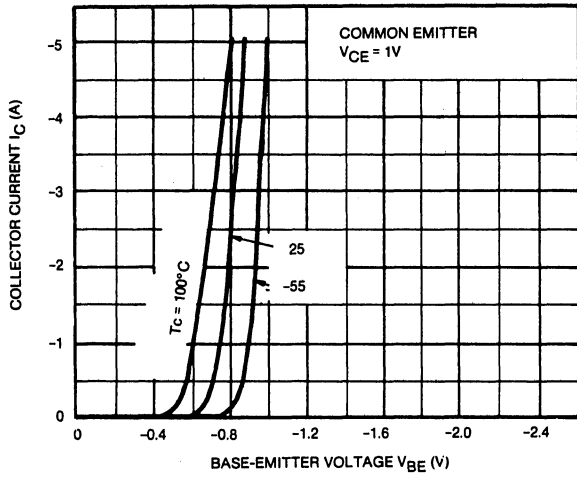


FIG. 9 $I_C - V_{BE}$

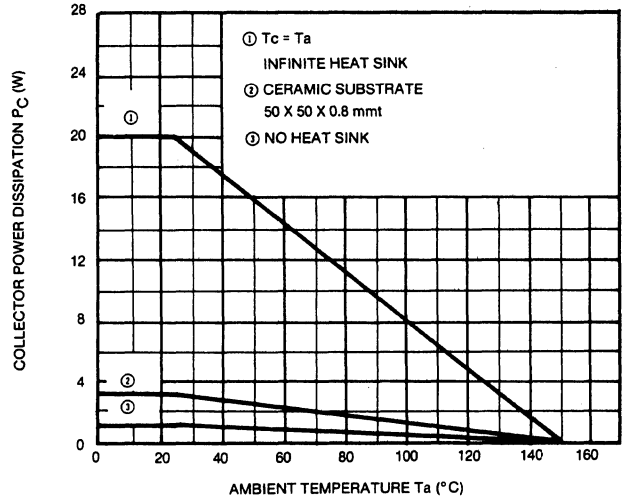


FIG. 10 $P_C - T_a$

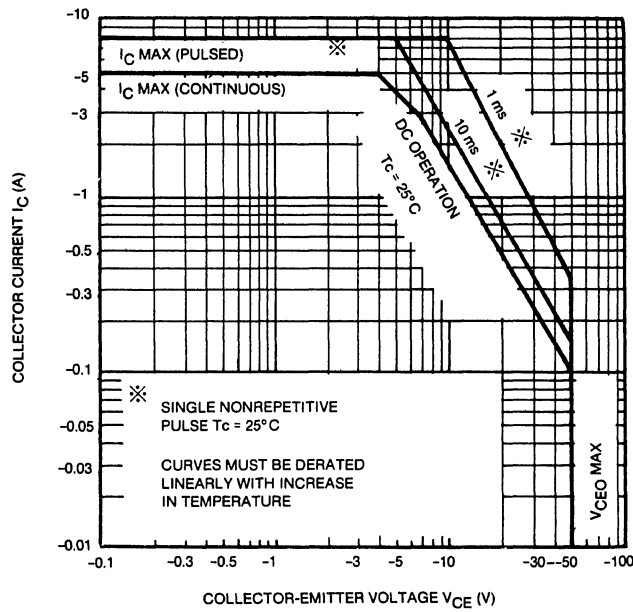


FIG. 11 SAFE OPERATING AREA